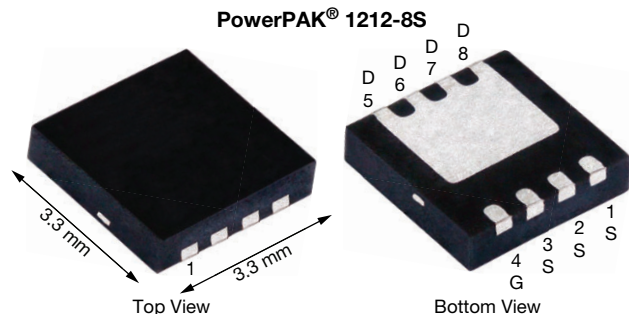


# N-Channel 45 V (D-S) MOSFET



## FEATURES

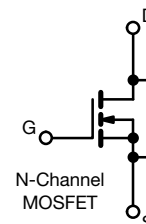
- TrenchFET® Gen IV power MOSFET
- Very low  $R_{DS(on)}$  in a compact and thermally enhanced package
- Optimized  $Q_g$ ,  $Q_{gd}$ , and  $Q_{gd}/Q_{gs}$  ratio reduces switching related power loss
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Synchronous rectification
- Synchronous buck converter
- High power density DC/DC
- Battery switching and protection
- Load switching



PRODUCT SUMMARY	
$V_{DS}$ (V)	45
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.00283
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.0041
$Q_g$ typ. (nC)	21.4
$I_D$ (A)	108
Configuration	Single

## ORDERING INFORMATION

Package	PowerPAK 1212-8S
Lead (Pb)-free and halogen-free	SiSS50DN-T1-GE3

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	45	V
Gate-source voltage	$V_{GS}$	+20 / -16	
Continuous drain current ( $T_J = 150^\circ\text{C}$ )	$I_D$	$T_C = 25^\circ\text{C}$	108
		$T_C = 70^\circ\text{C}$	86
		$T_A = 25^\circ\text{C}$	29.7 <sup>b, c</sup>
		$T_A = 70^\circ\text{C}$	23.7 <sup>b, c</sup>
Pulsed drain current ( $t = 100 \mu\text{s}$ )	$I_{DM}$	300	A
Continuous source-drain diode current	$I_S$	$T_C = 25^\circ\text{C}$	59.7
		$T_A = 25^\circ\text{C}$	4.5 <sup>b, c</sup>
Single pulse avalanche current	$I_{AS}$	30	
Single pulse avalanche energy	$E_{AS}$	45	mJ
Maximum power dissipation	$P_D$	$T_C = 25^\circ\text{C}$	65.7
		$T_C = 70^\circ\text{C}$	42
		$T_A = 25^\circ\text{C}$	5 <sup>b, c</sup>
		$T_A = 70^\circ\text{C}$	3.2 <sup>b, c</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Soldering recommendations (peak temperature) °C		260	

## THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient <sup>b</sup>	$R_{thJA}$	20	25	$^\circ\text{C}/\text{W}$
Maximum junction-to-case (drain)	$R_{thJC}$	1.5	1.9	

### Notes

- Package limited
- Surface mounted on 1" x 1" FR4 board
- $t = 10$  s
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is  $65^\circ\text{C}/\text{W}$
- $T_C = 25^\circ\text{C}$



SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	45	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	V <sub>DS</sub> temperature coefficient I <sub>D</sub> = 1 mA,	-	28	-	mV/°C
V <sub>GS(th)</sub> temperature coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>	V <sub>GS(th)</sub> temperature coefficient I <sub>D</sub> = 250 μA	-	-5.4	-	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.1	-	2.3	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +20, -16 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 45 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 45 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 75 °C	-	-	20	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	30	-	-	A
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	-	0.00225	0.00283	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A	-	0.0031	0.0041	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 15 A	-	72	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	4000	-	pF
Output capacitance	C <sub>oss</sub>		-	630	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	56	-	
C <sub>rss</sub> /C <sub>iss</sub> ratio			-	0.014	0.028	
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	-	46.7	70	nC
Gate-source charge	Q <sub>gs</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A	-	21.4	32	
Gate-drain charge	Q <sub>gd</sub>		-	11.1	-	
Output charge	Q <sub>oss</sub>		-	3.6	-	
Output charge	Q <sub>oss</sub>	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0 V	-	28	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.5	1.15	2	Ω
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	15	30	ns
Rise time	t <sub>r</sub>		-	6	12	
Turn-off delay time	t <sub>d(off)</sub>		-	30	60	
Fall time	t <sub>f</sub>		-	6	12	
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 20 V, R <sub>L</sub> = 2 Ω I <sub>D</sub> ≅ 10 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	30	60	
Rise time	t <sub>r</sub>		-	67	134	
Turn-off delay time	t <sub>d(off)</sub>		-	28	56	
Fall time	t <sub>f</sub>		-	10	20	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	-	-	50.9	A
Pulse diode forward current (t <sub>p</sub> = 100 μs)	I <sub>SM</sub>		-	-	300	
Body diode voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	-	0.72	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 15 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C	-	32	64	ns
Body diode reverse recovery charge	Q <sub>rr</sub>		-	24	48	nC
Reverse recovery fall time	t <sub>a</sub>		-	17	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	15	-	

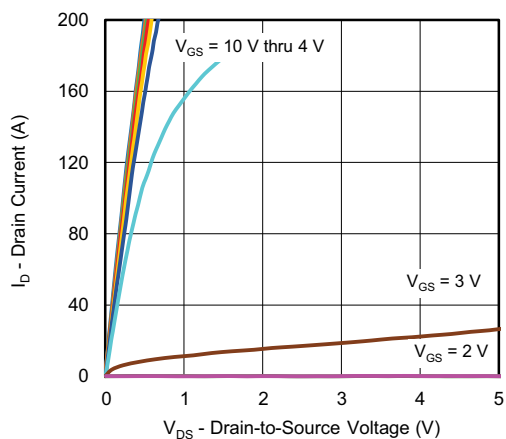
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing

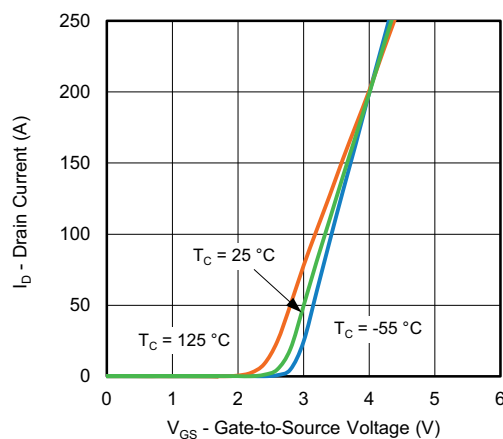
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



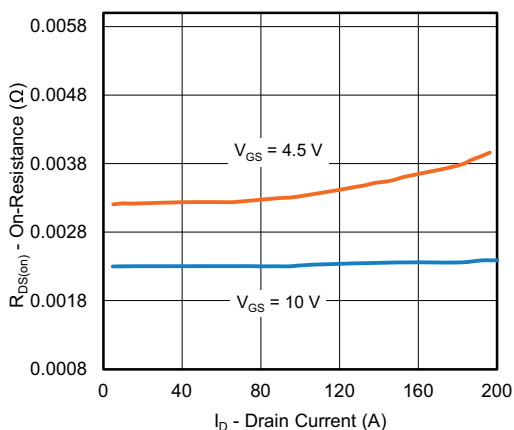
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



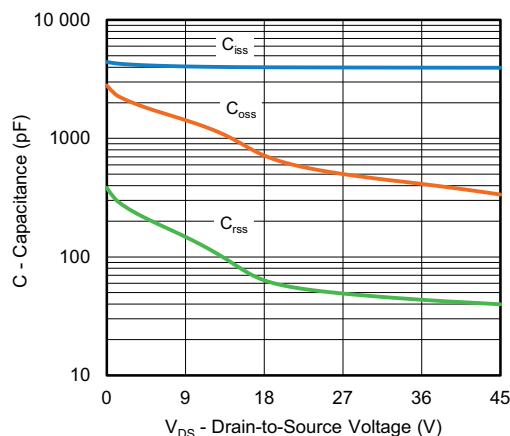
**Output Characteristics**



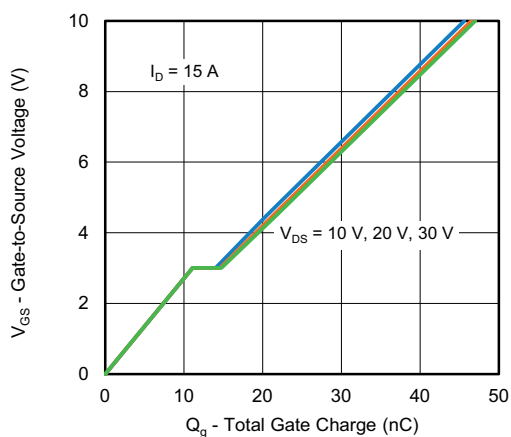
**Transfer Characteristics**



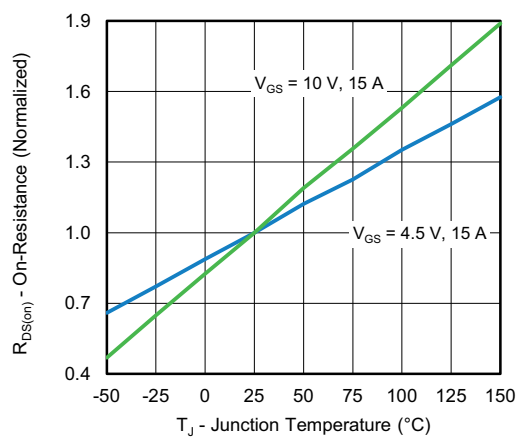
**On-Resistance vs. Drain Current**



**Capacitance**



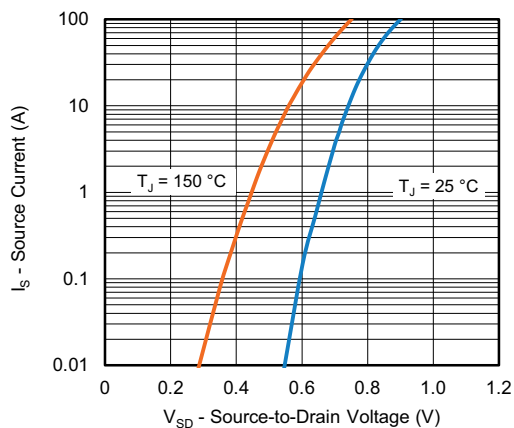
**Gate Charge**



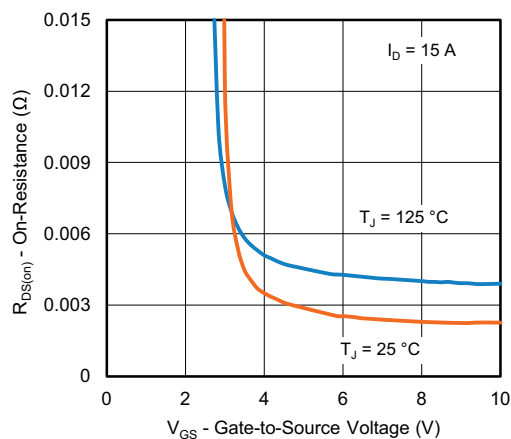
**On-Resistance vs. Junction Temperature**



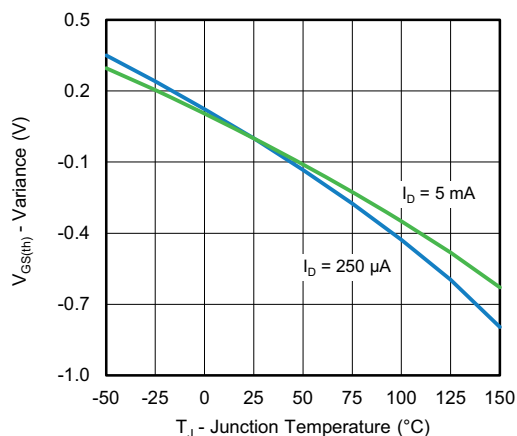
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



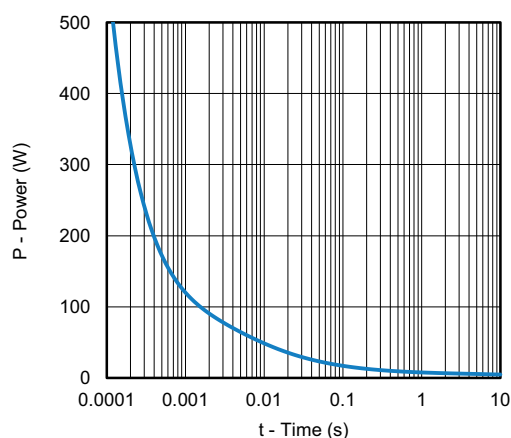
Source-Drain Diode Forward Voltage



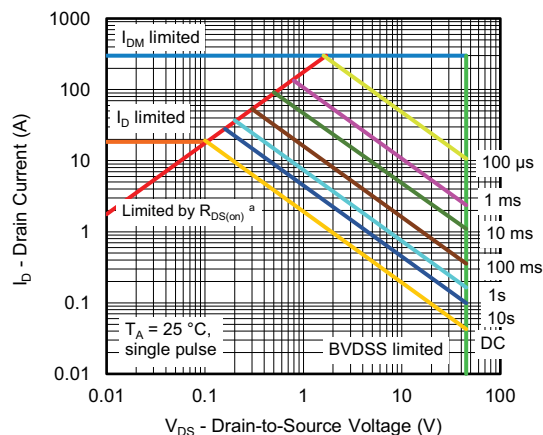
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



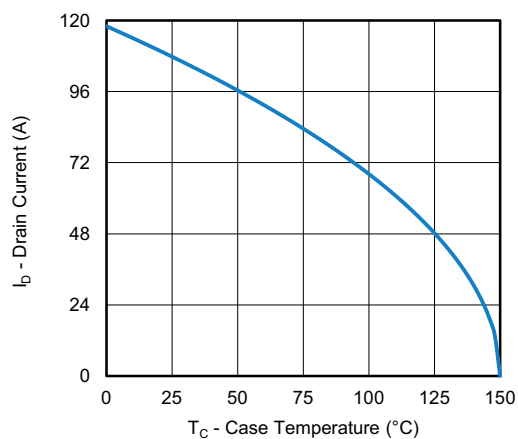
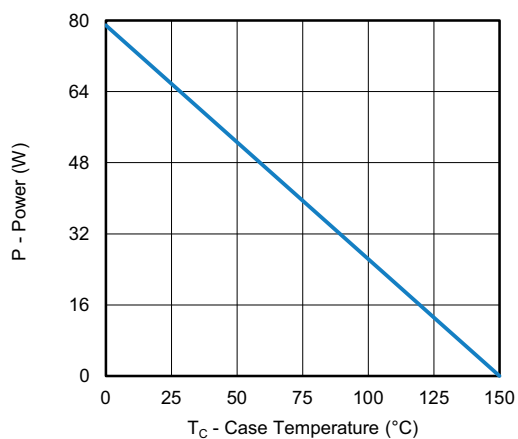
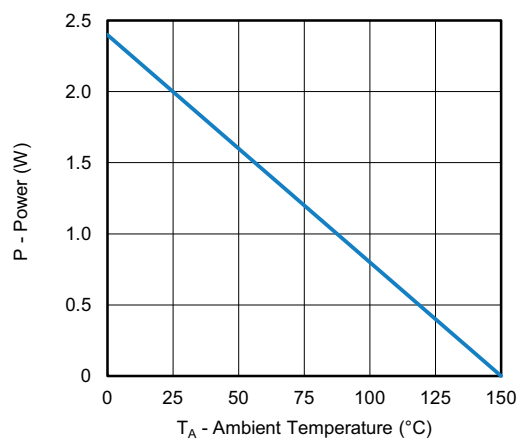
Single Pulse Power, Junction-to-Ambient



Safe Operating Area

**Note**

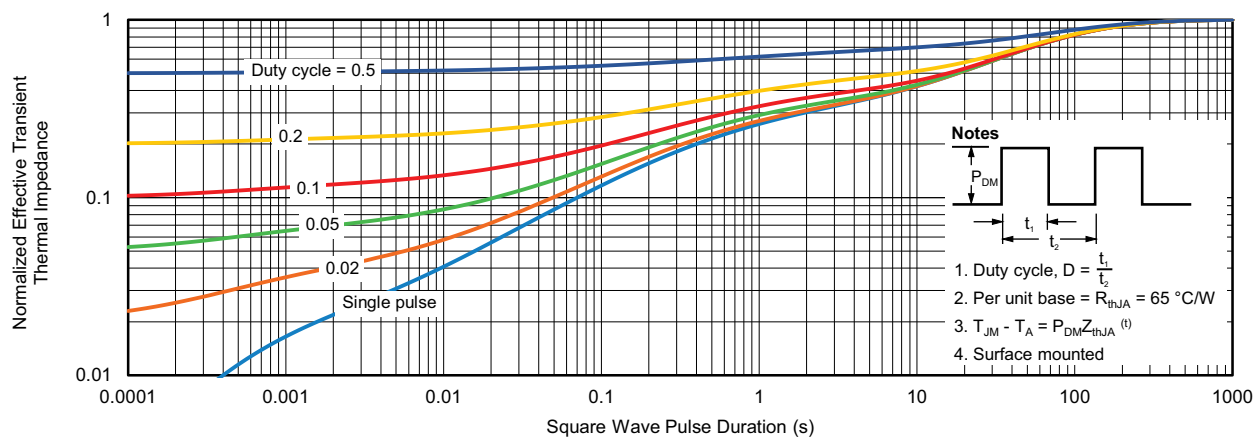
a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**

**Power, Junction-to-Ambient**
**Note**

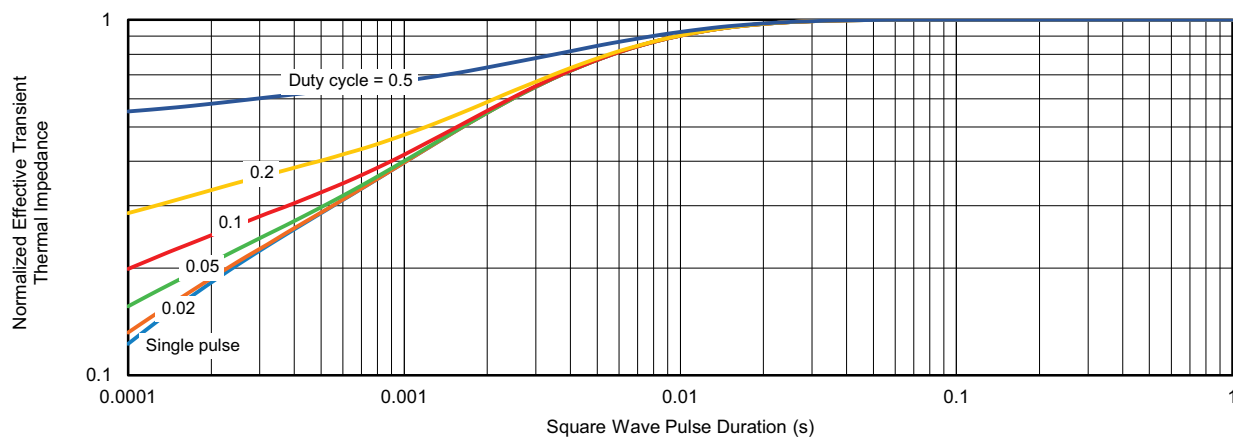
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

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